FIG.1

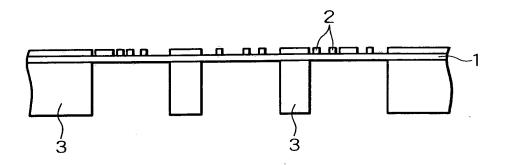


FIG.2

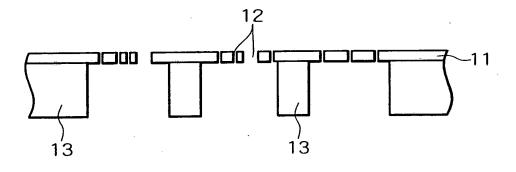


FIG.3

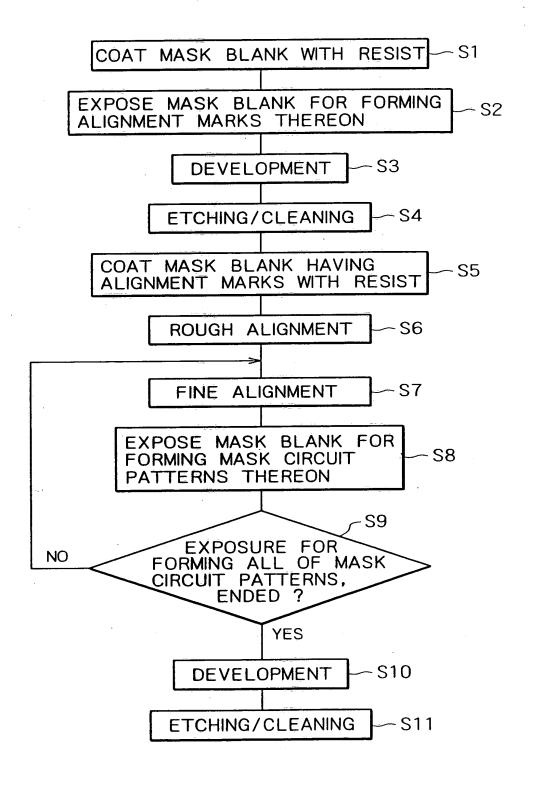


FIG.4A

REGION IN WHICH MASK CIRCUIT PATTERN IS TO BE FORMED

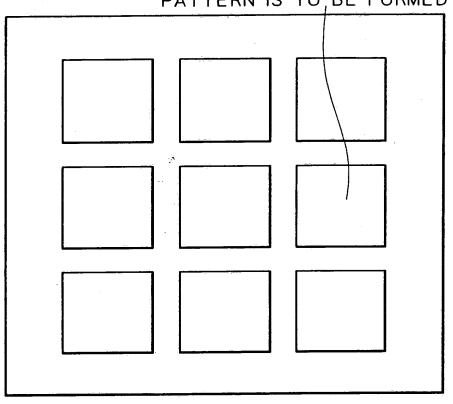


FIG.4B

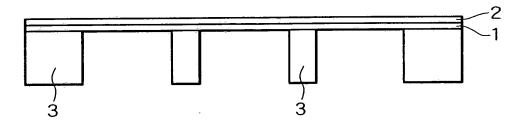


FIG.4C

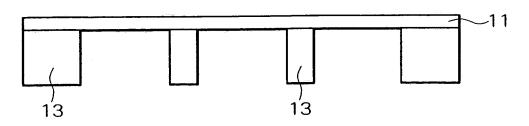


FIG.5A

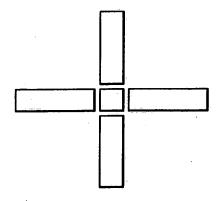


FIG.5B

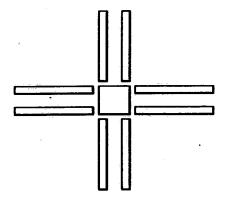


FIG.5C

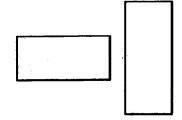


FIG.6

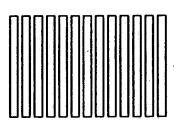




FIG.7A

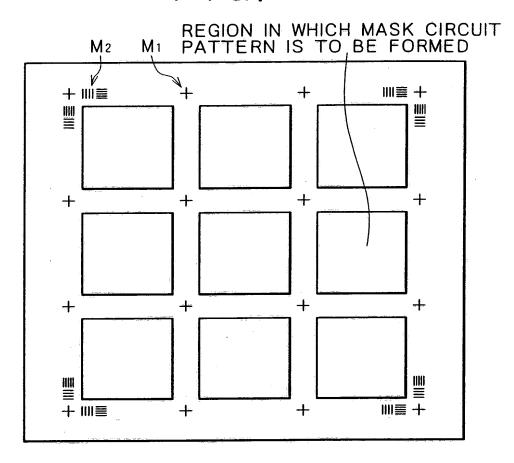


FIG.7B

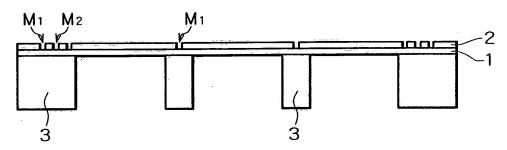


FIG.7C

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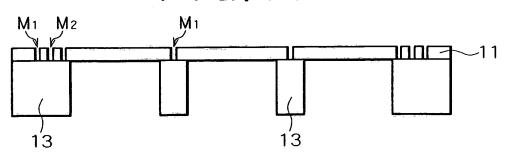
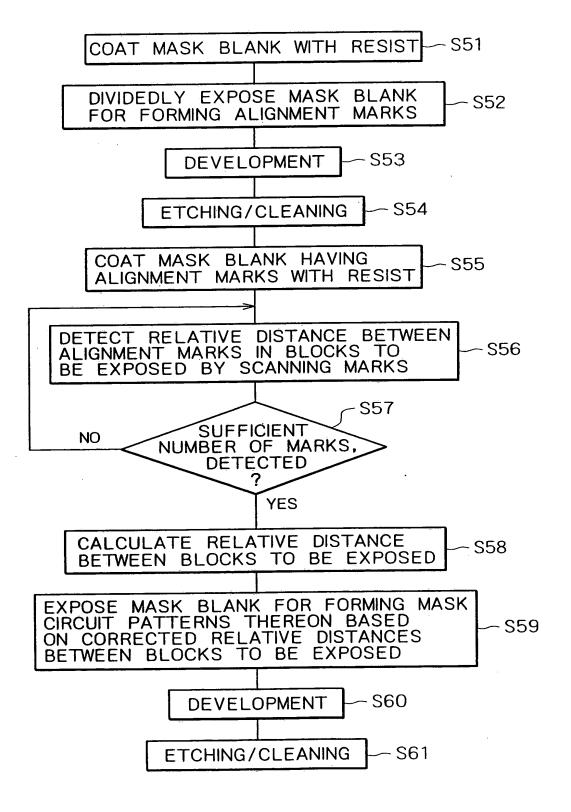


FIG.8



RESULT OF POSITIONAL DEVIATION MEASUREMENT CORRECTION AMOR FOR POSITIONAL DEVIATION ACCURACY CALCULATING SYSTEM (CALCULATION OF CORRECTION AMOUNT) WAFER ON WHICH POSITION MEASUREMEN PATTERN IS FORMED POSITIONAL MEASURING F 1 G. 9 TRANSFER EXPOSURE SYSTEM n TRANSFER EXPOSURE SYSTEM 2 EXPOSURE MASK EXPOSURE SYSTEM MASK TRANSFER ESYSTEM 1 TEST PREPARATION OF CORRECTED MASK CORRECTED MASK n CORRECTED MASK 2 CORRECTED MASK 1

FIG. 10

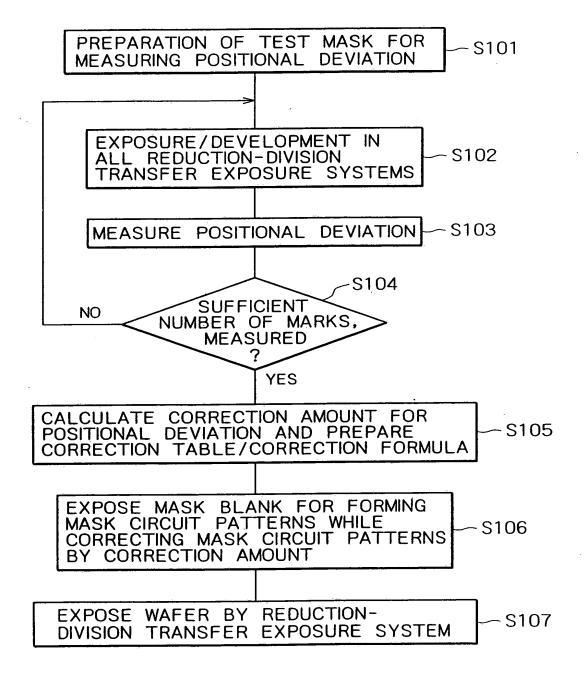


FIG. 11

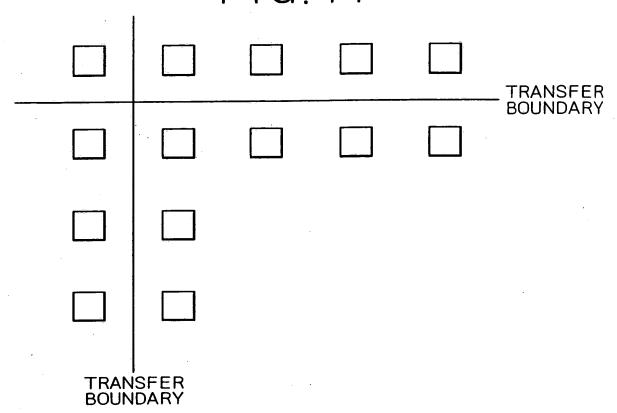


FIG. 12

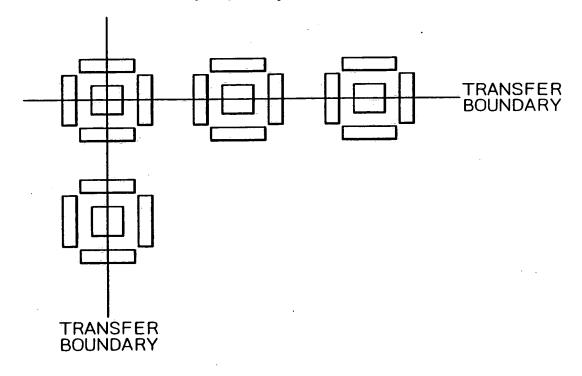


FIG. 13

